LTR	1	DESCRIPTION						IONS		DATE (YR-MO-DA)			APPROVED							
查询"	5962-	9218	301 IV	12A"1	共应		1111						DAT	<u>c (</u> 1K	-MU-DA	0	+	APPI	OVEL	
	I		÷										1				1			
REV SHEET																				
SHEET																				
SHEET REV	15	16	17	18	19	20	21	22												
SHEET REV SHEET REV STATL	L1 IS	16	17	18 RE\	1	20	21	22												
SHEET REV SHEET REV STATL	L1 IS	16	17	RE	1	20	21	22	3	4	5	6	7	8	9	10	11	12	13	1.
SHEET REV SHEET REV STATL OF SHEETS	L1 IS	16	17	RE SHE PREPA	V EET WRED BY	I	1		3		L	SE EL	ECTR	ONIC	s su	PPLY	CEN	1	13	1.
SHEET REV SHEET REV STATL OF SHEETS PMIC N/A STAND MIL	ARDI	ZED		REN SHE PREPA Wand CHECK	EET WRED BY	Y Y Meadow	1 s		3	נס	EFENS	SE EL	ECTR	ONIC	S SU HIO	PPLY 4544	CEN 44	TER.	I	1
SHEET REV SHEET REV STATL OF SHEETS PMIC N/A STAND MIL DRA THIS DRAWIN FOR USE BY A	ARDI ITAR WINK G IS AN	ZED XY G VAILAB	LE	REN SHE PREPA Wand CHECK Thom	EET ARED BY ta L. P KED BY nas J.	Y Meadow Ricci	1 s		3	DI MIC CMO	EFEN:	SE EL L IRCU	ECTR DAYTO	ONIC N, O DIC ERTE	S SU HIO HIO R W	PPLY 4544 L, A ITH	CEN 44 ADVA SCH	NCEI	 	1
SHEET REV SHEET REV STATL OF SHEETS PMIC N/A STAND MIL DR2 THIS DRAWIN	ARDI ITAR WINK G IS AN ALL DEP CIES OF	ZRD Y G VAILAB ARTMEN F THE	LE ITS	REN SHE PREPA Wand CHECK Thom APPRO Mon i	EET V RED BY ta L. F RED BY ta J. NED BY ica L.	Y Meadow Ricci	1 s uti ing DATE		3	DI MIC CMO TRI MON	EFENS ROC S, 1 GGE1 OLIS	SE EL I IRCU HEX R IN THIC	ECTR DAYTO	ONIC N, O DIG ERTE , TI LICC	S SU HIO HIO R W	PPLY 4544 L, A ITH	CEN 44 ADVA SCH	NCEI	 	1
SHEET REV SHEET REV STATL OF SHEETS PMIC N/A STANDA MILL DRA THIS DRAWIN FOR USE BY A AND AGEN	ARDI ITAR WINK G IS AV ALL DEP CIES OF T OF DE	ZRD Y G VAILAB ARTMEN F THE	LE ITS	REV SHE PREPA Wand CHECK Thom APPRO Mon i DRAWI	EET V RED BY ta L. F RED BY ta J. NED BY ica L.	Y Meadow Ricci Y Poelk Poelk 93-04	1 s uti ing DATE		3	DI MIC CMO TRI	EFENS ROC S, 1 GGE1 OLIS	SE EI IRCU HEX R IN FHIC	ECTR DAYTO	ONIC N, O DIC ERTE , TI LICC	S SU HIO HIO R W	PPLY 4544 L, A ITH OMPA	CEN 44 ADVA SCH ATIB	NCEI	D D T	1

٠

• ÷

.

JUL 91 <u>DISTRIBUTION STATEMENT A</u>. Approved for public release; distribution is unlimited.

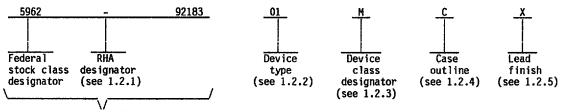
5962-E134-93

9004708 0005612 275 🔜

1. SCOPE

查询"5962-0218301102A"供应函数 of a one part - one part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes B, Q, and M) and space application (device classes S and V), and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of radiation hardness assurance (RHA) levels are reflected in the PIN.

1.2 <u>PIN</u>. The PIN shall be as shown in the following example:



Drawing number

1.2.1 <u>RHA designator</u>. Device classes M, B, and S RHA marked devices shall meet the MIL-M-38510 specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked devices shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 <u>Device type(s)</u>. The device type(s) shall identify the circuit function as follows:

<u>Device type</u>	<u>Generic number</u>	<u>Circuit function</u>
01	54ACTQ14	Hex inverter, TTL compatible, schmitt trigger inputs.

1.2.3 <u>Device class designator</u>. The device class designator shall be a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
М	Vendor self-certification to the requirements for non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883
B or S	Certification and qualification to MIL-M-38510
Q or V	Certification and qualification to MIL-I-38535

1.2.4 <u>Case outline(s)</u>. The case outline(s) shall be as designated in MIL-STD-1835, and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
C	GDIP1-T14 or CDIP2-T14	14	Dual-in-line
D	GDFP1-F14 or CDFP2-F14	14	Flat pack
2	CQCC1-N20	20	Leadless-chip-carrier

1.2.5 <u>Lead finish</u>. The lead finish shall be as specified in MIL-M-38510 for classes M, B, and S or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER -	SIZE A		5962-92183
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 2

DESC FORM 193A JUL 91

9004708 0005613 101 🔳

1.3 <u>Absolute maximum ratings</u> . <u>1/ 2/ 3</u> /				
查询"Supply Sates and Futures: 1) 上 5 查询"Supply Sates and Futures: 1) 上 5 DC input voltage range (V_{IN})	V _{CC} + 0.5 V) V _{CC} + 0.5 V)			
1.4 <u>Recommended operating conditions</u> . <u>1</u> / <u>2</u> / <u>3</u> /				
Supply voltage range (V_{CC})			+4.5 V dc 1 +0.0 V dc 1 +0.0 V dc 1 0.8 V 2.0 V -55°C to +] 125 mV/ns -24 mA +24 mA	to V _{CC}
1.5 <u>Digital logic testing for device classes Q and V</u> .				
Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012)		X	(X percent	<u>4</u> /
 Stresses above the absolute maximum rating may cause maximum levels may degrade performance and affect re for allowable short duration burn-in screening condi Unless otherwise specified, all voltages are referen The limits for the parameters specified herein shall range of -55°C to +125°C. 	liability. The m tions in accordan ced to GND. apply over the f	aximum junction ce with method 5 ull specified V _C	temperatur 004 of MIL	e may be exceeded -STD-883.
4/ Values will be added when they become available from	the qualified so	urce.		
STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A			5962-92183
DAYTON, OHIO 45444		REVISION L	EVEL	SHEET 3
DESC FORM 193A JUL 91				

9004708 0005614 048

٠

F

.

2. APPLICABLE DOCUMENTS

2. Government specifications, standards, bulletin, and handbook. Unless otherwise specified, the following specifications, standards, bulletin, and handbook of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATIONS

MILITARY

MIL-M-38510 MIL-I-38535	 Microcircuits, General Specification for. Integrated Circuits, Manufacturing, General Sp 	ecification for.
STANDARDS		

MILITARY

MIL-STD-480	- Configuration Control-Engineering Changes, Deviations and Waivers.	
MIL-STD-883 MIL-STD-1835	 Test Methods and Procedures for Microelectronics. Microcircuit Case Outlines. 	
112 010-1000		

BULLETIN

MILITARY

MIL-BUL-103 - List of Standardized Military Drawings (SMD's).

HANDBOOK

MILITARY

MIL-HDBK-780 - Standardized Military Drawings.

(Copies of the specifications, standards, bulletin, and handbook required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 <u>Non-Government publications</u>. The following documents form a part of this document to the extent specified herein. Unless otherwise specified, the issues of the documents which are DOD adopted are those listed in the issue of the DODISS cited in the solicitation. Unless otherwise specified, the issues of documents not listed in the DODISS are the issues of the documents cited in the solicitation.

ELECTRONIC INDUSTRIES ASSOCIATION (EIA)

JEDEC Standard No. 17 - A Standardized Test Procedure for the Characterization of the LATCH-UP in CMOS Integrated Circuits.

JEDEC Standard No. 20 - Standardized for Description of 54/74ACXXXX and 54/74ACTXXXX Advanced High-Speed CMOS Devices.

(Applications for copies should be addressed to the Electronics Industries Association, 2001 Eye Street, NW, Washington, DC 20006.)

(Non-Government standards and other publications are normally available from the organizations that prepare or distribute the documents. These documents may also be available in or through libraries or other informational services.)

2.3 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-92183
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 4

DESC FORM 193A JUL 91

90047080005615 T84 📟

3. REQUIREMENTS

The individual item requirements of MIL-M-38510. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes B and S shall be in accordance with MIL-M-38510 and as specified herein. This is a fully characterized military detail specification and is suitable for qualification of device classes B and S to the requirements of MIL-M-38510. The individual item requirements for device classes Q and V shall be in accordance with MIL-I-38535, the device manufacturer's Quality Management (QM) plan, and as specified herein.

3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 for device classes M, B, and S and MIL-I-38535 for device classes Q and V and herein.

3.2.1 <u>Case outline(s)</u>. The case outline(s) shall be in accordance with 1.2.4 herein.

3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 1.

3.2.3 <u>Iruth table</u>. The truth table shall be as specified on figure 2.

3.2.4 Logic diagram. The logic diagram shall be as specified on figure 3.

3.2.5 <u>Ground bounce waveforms and test circuit</u>. The ground bounce load circuit and waveforms shall be as specified on figure 4.

3.2.6 <u>Switching waveforms and test circuit</u>. The switching waveforms and test circuit shall be as specified on figure 5.

3.2.7 <u>Schematic circuits</u>. The schematic circuits shall be submitted to the preparing activity prior to the inclusion of a manufacturer's device in this drawing and shall be submitted to the qualifying activity as a prerequisite for qualification for device classes B and S. All qualified manufacturer's schematics shall be maintained and available upon request.

3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range. Test conditions for these specified characteristics and limits are as specified in table I. For device classes B and S, a pin-for-pin conditions and testing sequence for table I parameters shall be maintained and available upon request from the qualifying activity, on qualified devices.

3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes B and S shall be in accordance with MIL-M-38510. Marking for device classes Q and V shall be in accordance with MIL-I-38535.

3.5.1 <u>Certification/compliance mark</u>. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes B and S shall be a "J" or "JAN" as required in MIL-M-38510. The certification mark for device classes Q and V shall be a "QML" as required in MIL-I-38535.

3.5.2 <u>Correctness of indexing and marking for device classes B and S</u>. For device classes B and S, all devices shall be subjected to the final electrical tests specified in table II after PIN marking (marked in accordance with MIL-M-38510) to verify that they are correctly indexed and identified by PIN. Optionally, an approved electrical test may be devised especially for this requirement.

3.6 <u>Certificate of compliance</u>. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.3 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.2 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M the requirements of MIL-SID-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-I-38535 and the requirements herein.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-92183
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 5

DESC FORM 193A JUL 91

9004708 0005616 910 📟

查询"5962-92183 Test and MIL-STD-883 test		Test conditions unless otherwise specified $2/$ -55°C \leq T _C \leq +125°C	Device type <u>3</u> / and device	v _{cc}	Group A subgroups	Lim	its <u>2</u> /	Unit
method <u>1</u> /		$4.5 V \le V_{CC}^{\circ} \le 5.5 V$	class			Min	Max	
ligh level output voltage 3006	V _{OH1}	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0 V$ $V_{IL} = 0.8 V$ For all other inputs $V_{IN} = V_{CC}$ or GND $I_{OH} = -50 \mu A$	All	4.5 V	1,2,3	4.40		V
	V _{OH2}	For all inputs affecting output under test $V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{IH} = 2.0 V$ $V_{IL} = 0.8 V$ For all other inputs $V_{IN} = V_{CC} \text{ or GND}$ $I_{OH} = -50 \mu A$	All	5.5 V	1,2,3	5.40		
	V _{OH3}	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0 V$ $V_{IL} = 0.8 V$	A11	4.5 V	1	3.86		
		$V_{II}^{T} = 0.8 V$ For all other inputs $V_{IN} = V_{CC}$ or GND $I_{OH} = -24 \text{ mA}$			2,3	3.70		
	V _{OH4}	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0 V$ $V_{IL} = 0.8 V$	A11	5.5 V	1	4.86		
		$V_{IL} = 0.8 V$ For all other inputs $V_{IN} = V_{CC}$ or GND $I_{OH} = -24 \text{ mA}$			2,3	4.70		
	V _{OH5} <u>4</u> /	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0 V$ $V_{II} = 0.8 V$ For all other inputs $V_{IN} = V_{CC}$ or GND $I_{OH} = -50 \text{ mA}$	A11	5.5 V	1,2,3	3.85		
	of table. TANDARD ITARY D		SIZE				5962-9	2183
DEFENSE ELEC	TRONICS	S SUPPLY CENTER	Α		ISION LEV		HEET	

•

UESC FURM 193A JUL 91

9004708 0005617 857 📟

<u> </u>	1 IVI2A"1 Symbol	H.WTest conditions unless otherwise specified <u>2</u> / -55°C ≤ T _C ≤ +125°C 4.5 V ≤ V _{CC} ≤ 5.5 V	Device type <u>3</u> / and device	v _{cc}	Group A subgroups	Limi	its <u>2</u> /	Uni
	 	4.5 V S V _{CC} S 5.5 V	class			Min	Max	
Low level output voltage 3007	V _{OL1}	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0 V$ $V_{IL} = 0.8 V$ For all other inputs $V_{IN} = V_{CC}$ or GND $I_{OL} = 50 \mu A$	A11	4.5 V	1,2,3		0.10	V
	V _{OL2}	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0 V$ $V_{IL} = 0.8 V$ For all other inputs $V_{IN} = V_{CC}$ or GND $I_{OL} = 50 \mu A$	A11	5.5 V	1,2,3		0.10	
	V _{OL3}	For all inputs affecting output under test $V_{IN} = V_{IH}$ or V_{IL} $V_{IH} = 2.0 V$ $V_{IH} = 0.8 V$ For all other inputs	A11	4.5 V	1		0.36	
		$V_{II} = 0.8 V$ For all other inputs $V_{IN} = V_{CC}$ or GND $I_{OL} = 24 \text{ mA}$			2,3		0.50	
	V _{OL4}	For all inputs affecting output under test VIN = VIH Or VIL VIH = 2.0 V VIH = 0.8 V For all other inputs	A11	5.5 V	1		0.36	
		$V_{IL} = 0.8 V$ For all other inputs $V_{IN} = V_{CC}$ or GND $I_{OL} = 24 \text{ mA}$			2,3		0.50	
	V _{OL5}	For all inputs affecting output under test $V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{IH} = 2.0 \text{ V}$ $V_{II} = 0.8 \text{ V}$ For all other inputs $V_{IN} = V_{CC} \text{ or GND}$ $I_{OL} = 50 \text{ mA}$	A11	5.5 V	1,2,3		1.65	
	TANDARD		SIZE				5962-92	2183
DEFENSE ELEC	ITARY D TRONIC:	S SUPPLY CENTER	Α					

DESC FORM 193A JUL 91

•

📟 9004708 0005618 793 🎟

	Symbo1	otherwise specified 2/	Device type <u>3</u> / and device	v _{cc}	Group A subgroups	L1	imits <u>2</u> /	Uni
method 1/		$-55^{\circ}C \le T_{C} \le +125^{\circ}C^{-1}$ 4.5 V $\le V_{CC} \le 5.5$ V	class			Min	Max	
Positive input clamp voltage 3022	V _{IC+}	V _{CC} = GND For input under test I _{IN} = 1 mA	A11 B,S,Q,V		1	0.4	1.5	v
Negative input clamp voltage 3022	v _{IC-}	V _{CC} = Open For input under test I _{IN} = -1 mA	A11 B,S,Q,V		1	-0.4	-1.5	v
Input current high 3010	IIH	For input under test VIN = V _{CC} For all other inputs	A11	5.5 V	1	**	0.1	μA
		For ¹ äll other inputs V _{IN} - V _{CC} or GND			2,3		1.0	
Input current low 3009	IIL	For input under test V _{IN} - GND For all other inputs	A11	5.5 V	1		-0.1	μA
		For all other inputs V _{IN} - V _{CC} or GND			2,3		-1.0	
Input capacitance 3012	CIN	See 4.4.1d T _C = +25°C	A11	GND	4		10	pF
Power dissipation capacitance	CpD 5		A11	5.0 V	4		85	pF
Quiescent supply current delta,	^{∆1} cc	For input under test V _{IN} = V _{CC} - 2.1 V For all other inputs	A11	5.5 V	1		1.0	mA
TTL input levels 3005	<u>6</u> /	For all other inputs V _{IN} - V _{CC} or GND			2,3		1.6	
Quiescent supply current output	^I ССН	For all inputs affecting output under test	A11	5.5 V	1		4.0	μΑ
h igh 3005		V _{IN} = V _{CC} or GND			2,3		80	
Quiescent supply current output low	ICCL		A11	5.5 V	1		4.0	μΑ
3005					2,3		80	
Positive threshold voltage	V _{T+} 2/		A11	4.5 V	1,2,3		2.0	v
Negative threshold voltage	V _{T-} <u>8</u> /		11A	4.5 V	1,2,3	0.8		v
See footnotes at end	of table.							
MIL	TANDARI	DRAWING	SIZE A				5962-9	2183
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444				REV	ISION LE	VEL	SHEET	8

•

.

M 9004708 0005619 62T M

查询"5962-921830 Test and MIL-STD-883 test method 1/	1 M2A"(; Symbol	$\frac{1}{100}$ Test conditions unless otherwise specified 2/ -55°C \leq T _C \leq +125°C 4.5 V \leq V _{CC} \leq 5.5 V	Device type <u>3</u> / and device class	ype <u>3/</u> V _{CC} device	Group A subgroups	Limits <u>2</u> /		Unit
		4.5 V 4 V _{CC} 4 5.5 V	Class			Min	Max	
Hysteresis voltage	V _{HYS}	Calculated value: V _{HYS} = V _{T+} - V _{T-}	A11	4.5 V	1,2,3	0.4	1.2	V
Low level ground bounce noise	V _{ОLР} 97	V _{IH} = 3.0 V V _{IL} = 0.0 V T _A = +25 °C See figure 4	A11	5.0 V	4		1500	mV
Low level ground bounce noise	V9LV 9		A11	5.0 V	4		-1200	mV
High level V _{CC} bounce noise	V _{OHP} 97		A11	5.0 V	4		V _{ОН} +1000	mV
High level V _{CC} bounce noise	V _{ОНV} <u>9</u> /		All	5.0 V	4		V _{OH} -1200	mV
Latch-up input/ output over- voltage	I _{CC} (0/V1) <u>10</u> /	$\begin{array}{l} t_{w} \geq 100 \ \mu s \\ t_{cool} \geq t_{w} \\ 5 \ \mu s \leq t_{r} \leq 5 \ m s \\ 5 \ \mu s \leq t_{f} \leq 5 \ m s \\ V_{test} = 5.0 \ V \\ V_{CCQ} = 5.5 \ V \\ V_{over} = 10.5 \ V \end{array}$	A11 B,S,Q,V	5.5 V	2		200	mA
Latch-up input/ output positive over-current	I _{CC} (0/I1+) <u>10</u> /	$\begin{array}{l} t_w \geq 100 \ \mu s \\ t_{cool} \geq t_w \\ 5 \ \mu s \leq t_r \leq 5 \ m s \\ 5 \ \mu s \leq t_f \leq 5 \ m s \\ V_{test} = 6.0 \ V \\ V_{CCQ} = 5.5 \ V \\ I_{trigger} = +120 \ m A \end{array}$	A11 B,S,Q,V	5.5 V	2		200	mA
Latch-up input/ output negative over-current	^I CC (0/I1-) <u>10</u> /	$t_{w} \ge 100 \ \mu s$ $t_{cool} \ge t_{w}$ $5 \ \mu s \le t_{f} \le 5 \ m s$ $5 \ \mu s \le t_{f} \le 5 \ m s$ $V_{test} = 6.0 \ V$ $V_{CCQ} = 5.5 \ V$ $I_{trigger} = -120 \ mA$	A11 B,S,Q,V	5.5 V	2		200	mA
See footnotes at end o	f table.							
MILI	TANDARD	RAWING	SIZE A				5962-92	2183
DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444		45444		DEV	ISION LEV	/=1	SHEET	

DESC FORM 193A JUL 91

•

.

-

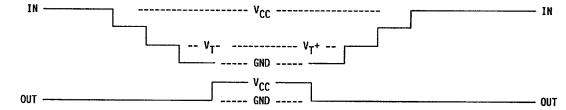
🔲 9004708 0005620 341 🖿

MIL-STD-883 test method <u>1</u> /	Symbol	$\frac{1277}{1657}$ conditions unless otherwise specified <u>2</u> / -55°C \leq T _C \leq +125°C 4.5 V \leq V _{CC} \leq 5.5 V	Device type <u>3</u> / and device class	Vcc	Group A subgroups	Lir Min	nits <u>2</u> /
Latch-up supply over-voltage	I _{CC} (0/v2) <u>10</u> /	$\begin{array}{l} t_{w} \geq 100 \ \mu s \\ t_{cool} \geq t_{w} \\ 5 \ \mu s \leq t_{f} \leq 5 \ m s \\ 5 \ \mu s \leq t_{f} \leq 5 \ m s \\ V_{test} = 6.0 \ V \\ V_{CCQ} = 5.5 \ V \\ V_{over} = 9.0 \ V \end{array}$	A11 B,S,Q,V	5.5 V	2		100
Truth table test output voltage	11/	V _{IL} = 0.8 V V _{IH} = 2.0 V	V All 4.	4.5 V	7,8	L	н
3014		Vêrify output V _O	A11	5.5 V	7,8	L	H
Propagation delay time, data to	tplh	C _L = 50 pF minimum R ₁ = 500Ω	A11 4.1 B,S,Q,V	4.5 V	9,11	1.0	11.0
output; I _n to O _n	12/	Sēe figure 5			10	1.0	12.5
3003			A11 M	4.5 V	9	1.0	11.0
					10,11	1.0	12.5
	t _{PHL}		A11 B,S,Q,V	4.5 V	9,11	1.0	10.0
	12/				10	1.0	11.5
			A11 M	4.5 V	9	1.0	10.0
				10,11	1.0	11.5	
Output skew 3003	t _{OSHL} , t _{OSLH} 13/		A11	4.5 V	9,10,11		1.0
2/ Each input/outpu minimum and VIL be verified duri tests multiple t low level logic, a. VIC (pos) te b. VIC (neg) te c. All ICC and shall be pla	t, as app maximum th ng each V ₀ imes to vo or open, sts, the V ΔI _{CC} tests ced in the led inform he qualify n designam d the abso	All inputs and outputs shal licable shall be tested at the mesholds for any input that the DL and VOH test. On some deverify all input thresholds. except as follows: GND terminal can be open. T VCC terminal shall be open. s, the output terminal shall e circuit such that all curre mation on qualified devices (ving activity (DESC-EQM) upon tes the potential difference olute value of the magnitude, sted herein. Devices shall m	e specified te may affect the ices, this will butput termina $C = +25^{\circ}C.$ $T_C = +25^{\circ}C.$ be open. When at flows throw i.e., pin for request. For in reference to not the sign,	emperature logic l requi als not perform ugh the main pin con negative to GND an , is rela	re for the state of th re repeatin designated ming these meter. ditions and ve and posi nd the dire ative to th	specified e output u g the same shall be f tests, the testing s tive volta ction of o e minimum	limits. inder test VOL and V igh level e current n equence) ige and cur urrent flo and maxim
values: The sig respectively; an limits, as appli 4.5 V ≤ V _{CC} ≤ 5.	5 V. specified	i, the word "All" in the devi	ce type and de	evice cla	ass column	means the	test is fo
values: The sig respectively; an limits, as appli 4.5 V ≤ V _{CC} ≤ 5. <u>3</u> / Unless otherwise device types and S MIII	5 V. specified classes. STANDARI	DIZED	ce type and de SIZE A	evice cl	ass column	means the	test is fo 5962-9

TABLE I. <u>Electrical performance characteristics</u> - Continued.

 $\frac{1}{2}$ Transmission driving teststating performed at V_{CC} = 5.5 V dc with a 2 ms duration maximum. This test may be performed using V_{IN} = V_{CC} or GND. When V_{IN} = V_{CC} or GND is used, the test is guaranteed for V_{IN} = 2.0 V or 0.8 V.

- 5/ Power dissipation capacitance (CpD) determines the power consumption. PD = (CpD + CL) (Vcc x Vcc)f + (Icc x Vcc) + (n x d x Δ Icc x Vcc). The current consumption, Is = (CpD + CL) Vccf + Icc + n x d x Δ Icc. For both PD and Is: n is the number of device inputs at TTL levels, f is the frequency of the input signal; and d is the duty cycle of the input signal.
- 6/ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}. This test may be performed either one input at a time (preferred method) or with all input pins simultaneously at V_{IN} = V_{CC} -2.1 V (alternate method). Classes B, S, Q, and V shall use the preferred method. When the test is performed using the alternate test method: the maximum limits is equal to the number of inputs at a high TTL input level times 1.6 mA or 1.0 mA, as applicable; and the preferred method and limits are guaranteed.
- \underline{I} / Increment input in 50 mV steps beginning 100 mV below the minimum limit specified until the output changes from V_{CC} to GND. The input voltage where this transition occurs is V_T +.



- $\underline{8}$ / Decrement input in 50 mV steps beginning 100 mV above the maximum limit specified until the output changes from GND to V_{CC}. The input voltage where this transition occurs is V_T-.
- 9' This test is for qualification only. Ground and V_{CC} bounce tests are performed on a non-switching (quiescent) output and are used to measure the magnitude of induced noise caused by other simultaneously switching outputs. The test is performed on a low noise bench test fixture. For the device under test, all outputs shall be loaded with 500 Ω of load resistance and a minimum of 50 pF of load capacitance (see figure 4). Only chip capacitors and resistors shall be used. The output load components shall be located as close as possible to the device outputs. It is suggested, that whenever possible, this distance be kept to less than .25 inches. Decoupling capacitors shall be placed in parallel from V_{CC} to ground. The values of these decoupling capacitors shall be the device manufacturer. The low and high level ground and V_{CC} bounce noise is measured at the quiet output using a 1 GHz minimum bandwidth oscilloscope with a 50 Ω input impedance.

The device inputs shall be conditioned such that all outputs are at a high nominal V_{OH} level. The device inputs shall then be conditioned such that they switch simultaneously and the output under test remains at V_{OH} as all other outputs possible are switched from V_{OH} to V_{OL} . V_{OHV} and V_{OHP} are then measured from the nominal V_{OH} level to the largest negative and positive peaks, respectively (see figure 4). This is then repeated with the same outputs not under test switching from V_{OL} to V_{OH} .

The device inputs shall be conditioned such that all outputs are at a low nominal V_{OL} level. The device inputs shall then be conditioned such that they switch simultaneously and the output under test remains at V_{OL} as all other outputs possible are switched from V_{OL} to V_{OH}. V_{OLP} and V_{OLV} are then measured from the nominal V_{OL} level to the largest positive and negative peaks, respectively (see figure 4). This is then repeated with the same outputs not under test switching from V_{OH} to V_{OL}.

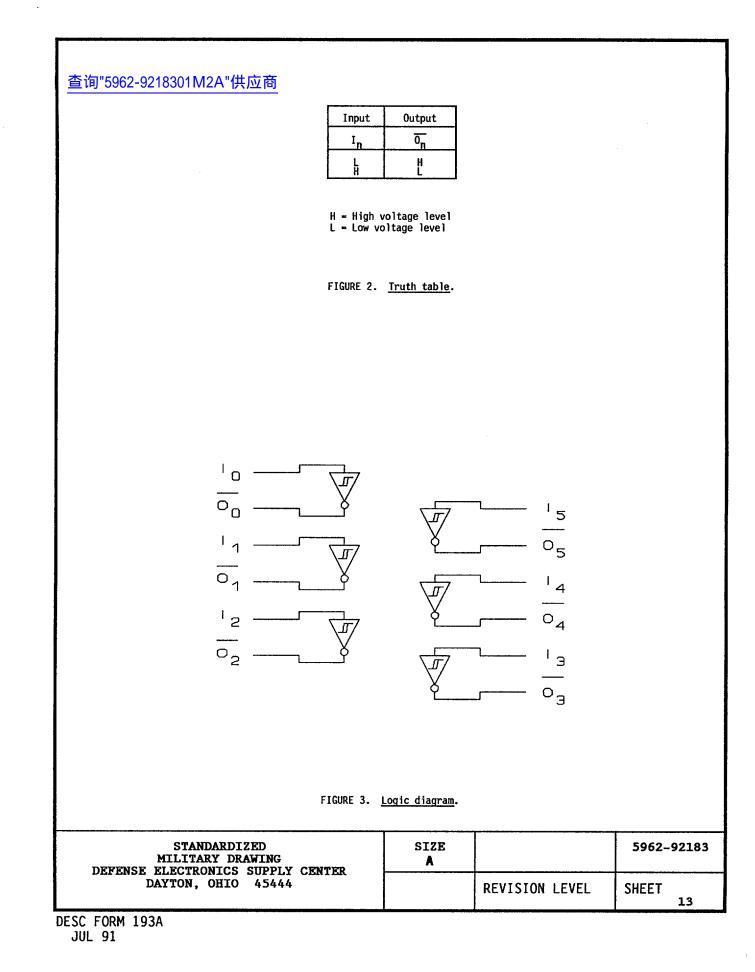
- 10/ See JEDEC STD. 17 for electrically induced latch-up test methods and procedures. The values listed for Vtrigger, Itrigger and Vover, are to be accurate within ±5 percent.
- <u>11</u>/ Tests shall be performed in sequence, attributes data only. Functional tests shall include the truth table and other logic patterns used for fault detection. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2 herein. Functional tests shall be performed in sequence as approved by the qualifying activity on qualified devices. $H \ge 2.5 V$, L < 2.5 V.
- <u>12</u>/ AC limits at V_{CC} = 5.5 V are equal to the limits at V_{CC} = 4.5 V and guaranteed by testing at V_{CC} = 4.5 V. Minimum propagation delay time limits for V_{CC} = 5.5 V are 1.0 ns and guaranteed by guard-banding the V_{CC} = 4.5 V minimum limits to 1.5 ns. For propagation delay tests, all paths must be tested.
- 13/ This parameter is guaranteed, if not tested, to the limits specified in Table I herein. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either high-to-low (t_{OSHL}) or low-to-high (t_{OSLH}).

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-92183
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 11

DESC FORM 193A JUL 91

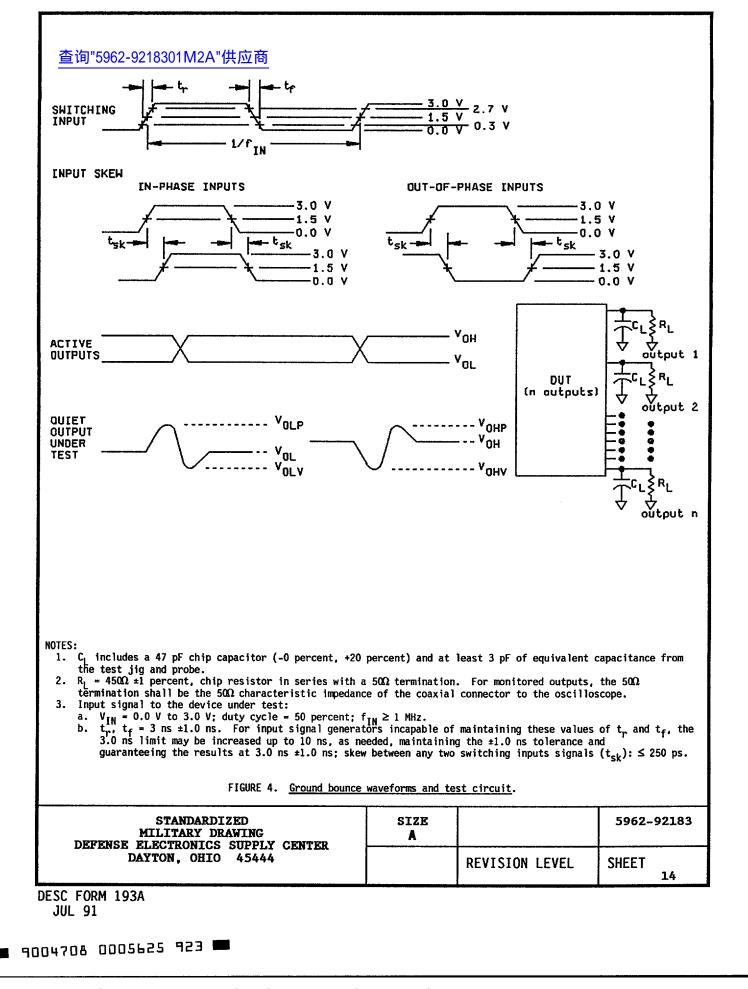
9004708 0005622 114 📟

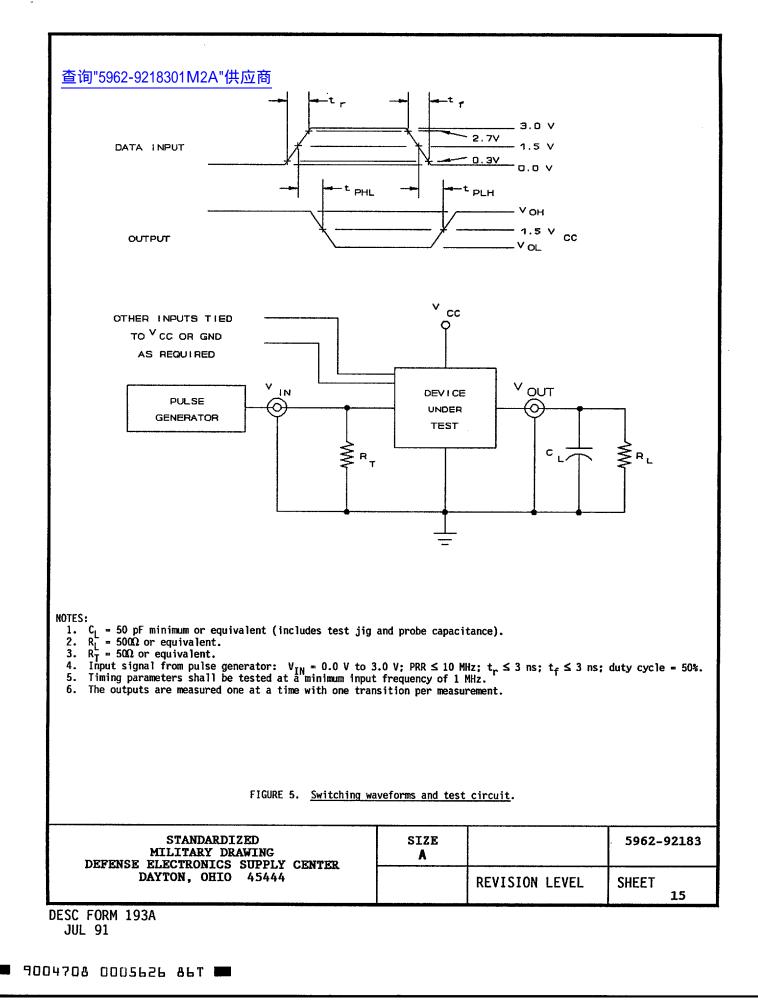
ī询"5962-9218301M2A	Device type	0	1			
111 0902-92183011VIZA	1共应向 Case outlines	C,D	2			
	Terminal number	Terminal	symbol			
	1	¹ 0	NC			
	2	0 ₀	I O			
	3	I ₁	00			
	4	<u>0</u> 1	^I 1			
	5	^I 2	NC			
	6	02	$\overline{0_1}$			
	7	GND	NC			
	8	0 ₃	¹ 2			
	9	^I 3	02			
	10	04	GND			
	11	I ₄	NC			
	12	05	0 ₃			
	13	¹ 5	I ₃			
	14	v _{cc}	$\overline{o_4}$			
	15		NC			
	16		^I 4			
	17		NC			
	18		0 ₅			
	19		I ₅			
	20		v _{cc}			
Terminal symbol I _n (n = 0 to 5)			Descrip inputs ts (inve			
L	0 _n (n = 0 to 5) FIGURE 1. <u>Term</u>	-		rting)		
STANDARI MILITARY I DEFENSE ELECTRONIC	RAWING S SUPPLY CENTER	SIZE A			5962-9	9218:
DAYTON, OHI	0 45444		R	EVISION LEVEL	SHEET	12
FORM 193A						1:



9004708 0005624 797 📰

.





3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1.4erein) or device classes B and S in MIL-M-38510 or for device classes Q and V in MIL-I-38535 shall be provided with each loc of microelincutty devivered to this drawing.

3.8 <u>Notification of change for device class M</u>. For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-480.

3.9 <u>Verification and review for device class M</u>. For device class M, DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 <u>Microcircuit group assignment for device classes M, B, and S</u>. Device classes M, B, and S devices covered by this drawing shall be in microcircuit group number 37 (see MIL-M-38510, appendix E).

3.11 <u>Serialization for device class S</u>. All device class S devices shall be serialized in accordance with MIL-M-38510.

4. QUALITY ASSURANCE PROVISIONS

4.1 <u>Sampling and inspection</u>. For device class M, sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein). For device class B, sampling and inspection procedures shall be in accordance with MIL-M-38510 and method 5005 of MIL-STD-883, except as modified herein. For device class S, sampling and inspection procedures shall be in accordance with MIL-M-38510 and methods 5005 and 5007 of MIL-STD-883, except as modified herein. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-I-38535 and the device manufacturer's QM plan.

4.1.1 <u>Burn-in and life test circuits</u>. For device classes B and S, the burn-in and life test circuits shall be constructed so that the devices are stressed at the maximum operating conditions stated in 4.2.1a(5) or 4.2.1a(6) as applicable, or equivalent as approved by the qualifying activity.

4.2 <u>Screening</u>. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes B and S, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to qualification and quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. The following additional criteria shall apply.

- 4.2.1 Additional criteria for device classes M, B, and S.
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C or D. For device class M, the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. For device classes B and S, the test circuit shall be submitted to the qualifying activity. For device classes M, B, and S, the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - (3) Delete the sequence specified in 3.1.10 through 3.1.14 of method 5004 and substitute the first 7 test requirements of table II herein.
 - (4) For device class M, unless otherwise specified, the requirements for device class B in method 1015 of MIL-STD-883 shall be followed.
 - (5) Static burn-in, device classes B and S, test condition A, test method 1015 of MIL-STD-883. The test duration for each static test shall be 24 hours minimum for class S devices and in accordance with table I of method 1015 for class B devices.
 - (a) For static burn-in I, all inputs shall be connected to GND. Outputs may be open or connected to $V_{CC}/2 \pm 0.5 \text{ V}$. Resistors RI are optional on both inputs and open outputs, and required on outputs connected to $V_{CC}/2 \pm 0.5 \text{ V}$. RI = 220 Ω to 47 k Ω .

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-92183
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 16

DESC FORM 193A JUL 91

9004708 00056277T6 🔳

(b) For static burn-in II, all inputs shall be connected through the RI resistors to V_{CC} . Outputs may be open or connected to $V_{CC}/2 \pm 0.5 \text{ V}$. Resistors R1 are optional on open outputs, and required on 10^{15} 5062-921 outputs connected to $V_{CC}/2 \pm 0.5 \text{ V}$. R1 = 220 Ω to 47 k Ω .

(c) $V_{CC} = 5.5 V + 0.5 V, -0.00 V.$

- (6) Dynamic burn-in, device classes B and S, test condition D, method 1015 of MIL-STD-883.
 - (a) Input resistors = 220Ω to 2 k Ω ±20 percent.
 - (b) Output resistors = 220Ω ±20 percent.
 - (c) $V_{CC} = 5.5 V + 0.5 V$, -0.00 V.
 - (d) All inputs shall be connected through the resistors in parallel to a common clock pulse (CP). Outputs shall be connected to $V_{CC}/2 \pm 0.5$ V through the resistors.
 - (e) CP = 25 kHz to 1 MHz square wave; duty cycle = 50 percent ±15 percent; V_{IH} = 4.5 V to V_{CC} , V_{IL} = 0 V ±0.5 V; t_r , $t_f \le 100$ ns.
- b. Interim and final electrical test parameters shall be as specified in table II herein.
- c. For class S devices, post dynamic burn-in, or class B devices, post static burn-in, electrical parameter measurements may, at the manufacturer's option, be performed separately or included in the final electrical parameter requirements.
- 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-I-38535 and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - b. Interim and final electrical test parameters shall be as specified in table II herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535.
- 4.2.3 Percent defective allowable (PDA).
 - a. The PDA for class S devices shall be 5 percent for static burn-in and 5 percent for dynamic burn-in, based on the exact number of devices submitted to each separate burn-in.
 - b. Static burn-in I and II failures shall be cumulative for determining the PDA.
 - c. The PDA for class B devices shall be in accordance with MIL-M-38510 for static burn-in. Dynamic burn-in is not required.
 - d. The PDA for class M devices shall be in accordance with MIL-M-38510 for static burn-in and dynamic burn-in.
 - e. Those devices whose measured characteristics, after burn-in, exceed the specified delta limits or electrical parameter limits specified in table I, subgroup 1, are defective and shall be removed from the lot. The verified number of failed devices times 100 divided by the total number of devices in the lot initially submitted to burn-in shall be used to determine the percent defective for the lot and the lot shall be accepted or rejected based on the specified PDA.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444	SIZE A		5962-92183
		REVISION LEVEL	SHEET 17

DESC FORM 193A JUL 91

9004708 0005628 632 📟

木		ABLE II. <u>Ele</u>	ctrical test re	equirements.					
旦	词 "5962-9218301M2A"供应商 Test requirements, MIL-SID-883 test method (one part - one	(per	Subgroups <u>1</u> method 5005, ta	/ able I)	Subgrou (per MIL-I-385	ps <u>1</u> / 35, table III)			
	part number reference paragraph)	Device class M	Device class B <u>2</u> /	Device class S <u>2</u> /	Device class Q	Device class V			
	Interim electrical parameters, method 5004		1	1	1	1			
	Static burn-in I, method 1015 (4.2.1a)	<u>3</u> /	Not required	Required <u>4</u> /	Not required	Required <u>4</u> /			
	Interim electrical parameters, method 5004 (4.2.1b)			1 <u>5</u> /		1 <u>5</u> /			
	Static burn-in II, method 1015 (4.2.1a)	<u>3</u> /	Required <u>6</u> /	Required	Required <u>6</u> /	Required <u>4</u> /			
	Interim electrical parameters, method 5004 (4.2.1b)		1 <u>2/ 5</u> /	1 <u>2/5</u> /	1 <u>2/ 5</u> /	1 2/5/			
	Dynamic burn-in I, method 1015 (4.2.1a)	<u>3</u> /	Not required	Required <u>4</u> /	Not required	Required <u>4</u> /			
	Interim electrical parameters, method 5004 (4.2.1b)			1 <u>5</u> /		1 <u>5</u> /			
	Final electrical parameters, method 5004	1,2,3, 7,8,9 <u>2</u> /	1.2.7.9 <u>2/ 6</u> /	1,2,7.9 <u>2</u> /	1,2,3,7,8,9, 10,11 <u>2/ 6</u> /	1,2,3,7,8,9, 10,11 <u>2</u> /			
	Group A test requirements, method 5005 (4.4.1)	1,2,3,4,7, 8,9,10,11	1,2,3,4,7, 8,9,10,11	1,2,3,4,7, 8,9,10,11	1,2,3,4,7, 8,9,10,11	1,2,3,4,7, 8,9,10,11			
	Group B end-point electrical parameters, method 5005 (4.4.2)			1,2,3,7,8, 9,10,11 <u>5</u> /					
	Group C end-point electrical parameters, method 5005 (4.4.3)	1,2,3	1,2 <u>5</u> /		1,2,3 <u>5</u> /	1,2,3,7,8, 9,10,11 <u>5</u> /			
	Group D end-point electrical parameters, method 5005 (4.4.4)	1,2,3	1,2	1,2,3	1,2,3	1,2,3			
	Group E end-point electrical parameters, method 5005 (4.4.5)	1,7,9	1,7,9	1,7,9	1,7,9	1,7,9			
	1/ Blank spaces indicate tests are	not applicable	•						
	2/ PDA applies to subgroup 1 (see 4 4.2.3).	.2.3). For de	vice classes S	and V, PDA app	lies to subgroup	s 1 and 7 (see			
	3/ The required test condition used compliance, see 4.2.1a herein.	for burn-in s	hall be that s	ubmitted to DES	C-EC with the ce	rtificate of			
	4/ On all class S lots, the device a burn-in electrical parameters (gr preburn-in and interim electrica	roup A, subgro	up 1), in acco	rdance with tes	t method 5004 of	MIL-STD-883. For			
	5/ Delta limits shall be required on to the previous interim electrica	nly on table I al parameters.	, subgroup 1. The delta lin	The delta valu mits are specif	es shall be comp ied in table III	uted with reference			
	6/ The device manufacturer may at his option either complete subgroup 1 electrical parameter measurements. including delta measurements, within 96 hours after burn-in completion (removal of bias; or may complete subgroup 1 electrical measurements without delta measurements within 24 hours after burn-in completion (removal of bias). When the manufacturer elects to perform the subgroup 1 electrical parameter measurements without delta measurements, there is no requirement to perform the pre-burn-in electrical tests (first interim electrical parameters test in table II).								
	STANDARDIZED MILITARY DRAWING	2 (12)10120	SIZI A	3		5962-92183			
	DEFENSE ELECTRONICS SUPPLY DAYTON, OHIO 45444			REVIS	ION LEVEL	SHEET 18			
FCC	FORM 193A								

DESC FORM 193A JUL 91

9004708 0005629 579 📟

Delta	lim	its	at	+25°	'C.

询"5962-9218301M2A"供	立高 arameter <u>1</u> /	Device types	Limits
	ICCL. ICCH. ICCZ	A11	±100 nA

1/ The parameters shall be recorded before and after the required burn-in and life tests to determine delta limits.

4.3 Qualification inspection.

查

4.3.1 <u>Qualification inspection for device classes B and S</u>. Qualification inspection for device classes B and S shall be in accordance with MIL-M-38510. Inspections to be performed shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5).

4.3.2 <u>Qualification inspection for device classes Q and V</u>. Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5).

4.3.3 <u>Electrostatic discharge sensitivity qualification inspection</u>. Electrostatic discharge sensitivity (ESDS) testing shall be performed in accordance with MIL-STD-883, method 3015. ESDS testing shall be measured only for initial qualification and after process or design changes which may affect ESDS classification.

4.4 <u>Conformance inspection</u>. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Quality conformance inspection for device classes B and S shall be in accordance with MIL-M-38510 and as specified herein. Inspections to be performed for device classes M, B, and S shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5). Technology conformance inspection for classes Q and V shall be in accordance with MIL-I-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.

4.4.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. Latch-up tests are required for all device classes. These tests shall be performed only for initial qualification and after process or design changes which may affect the performance of the device. Latch-up tests shall be considered destructive. Test all applicable pins on five devices with zero failures.
- c. Ground and V_{CC} bounce tests are required for all device classes. These tests shall be performed only for initial qualification, after process or design changes which may affect the performance of the device, and any changes to the test fixture. V_{OLP} , V_{OLV} , V_{OHP} , and V_{OHV} shall be measured for the worst case outputs of the device. All other outputs shall be guaranteed, if not tested, to limits established for the worst case outputs. The worst case outputs tested are to be determined by the manufacturer. Test 5 devices assembled in the worst case package type supplied to this document. All other package types shall be guaranteed, if not tested, to limits established for the worst case package. The package type to be tested shall be determined by the manufacturer. The device manufacturer will submit to DESC data that shall include all measured peak values for each device tested and detailed oscilloscope plots for each V_{OLP} , V_{OLV} , V_{OHP} , and V_{OHV} from one sample part per function. The plot shall contain the waveforms of both a switching output and the output under test.

Each device manufacturer shall test product on the fixtures they currently use. When a new fixture is used, the device manufacturer shall inform DESC-EC of this change and test the 5 devices on both the new and old test fixtures. The device manufacturer shall then submit to DESC-EC data from testing on both fixtures, that shall include all measured peak values for each device tested and detailed oscilloscope plots for each V_{OLP} , V_{OLP} , and V_{OHP} , from one sample part per function. The plot shall contain the waveforms of both a switching output and the output under test.

d. C_{IN} , C_{OUT} , and C_{PD} shall be measured only for initial qualification and after process or design changes which may affect capacitance. C_{IN} and C_{OUT} shall be measured between the designated terminal and GND at a frequency of 1 MHz. C_{PD} shall be tested in accordance with the latest revision of JEDEC Standard No. 20 and table I herein. For C_{IN} , C_{OUT} , and C_{PD} , test all applicable pins on five devices with zero failures.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-92183
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 19

DESC FORM 193A JUL 91

9004708 0005630 290 🎟

e. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table in figure 2 herein. 查询 The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2 herein. For device classes B and S, subgroups 7 and 8 tests shall be sufficient to verify the truth table as approved by the qualifying activity. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).

4.4.2 <u>Group B inspection</u>. The group B inspection end-point electrical parameters shall be as specified in table II herein and as follows.

- a. Class S steady-state life (accelerated) shall be conducted using test condition D of method 1005 of MIL-STD-883 and the circuit described in 4.2.1a(6) herein, or equivalent as approved by the qualifying activity. For device class S steady-state life tests, the test circuit shall be submitted to the qualifying activity.
- b. End-point electrical parameters shall be as specified in table II herein. Delta limits shall apply only to subgroup 5 of group 8 inspections and shall consist of tests specified in table III herein.

4.4.3 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.3.1 <u>Additional criteria for device classes M and B</u>. Steady-state life test conditions, method 1005 of MIL-STD-883:

- a. End-point electrical parameters shall be as specified in table II herein. Delta limits shall apply only to subgroup 1 of group C inspection and shall consist of tests specified in table III herein.
- b. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - (1) Test condition A, B, C or D. For device class M, the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. For device class B, the test circuit shall be submitted to the qualifying activity. For device classes M and B, the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (2) $T_A = +125^{\circ}C$, minimum.
 - (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.3.2 <u>Additional criteria for device classes Q and V</u>. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's TRB in accordance with MIL-I-38535 and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.

4.4.4 <u>Group D inspection</u>. Group D inspection shall be in accordance with table IV of method 5005 of MIL-STD-883. End-point electrical parameters shall be as specified in table II herein.

4.4.5 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes B, S, Q, and V shall be M, D, R, and H and for device class M shall be M and D.

- a. End-point electrical parameters shall be as specified in table II herein.
- b. For device classes M, B, and S, the devices shall be subjected to radiation hardness assured tests as specified in MIL-M-38510 for the RHA level being tested. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-M-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as specified in table I at $T_A = +25^{\circ}$ C, after exposure, to the subgroups specified in table II herein.

c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE A		5962-92183
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 20

DESC FORM 193A JUL 91

9004708 0005631 127 🖿

4.5 <u>Methods of inspection</u>. Methods of inspection shall be specified as follows:

查询159<u>62tage1anaOcuMene</u>."供应药otherwise specified, all voltages given are referenced to the microcircuit GND terminal. Currents given are conventional current and positive when flowing into the referenced terminal.

5. PACKAGING

. .

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-M-38510 for device classes M, B, and S and MIL-I-38535 for device classes Q and V.

6. NOTES

6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.1.2 <u>Substitutability</u>. Device classes B and Q devices will replace device class M devices.

6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).

6.3 <u>Record of users</u>. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.

6.4 <u>Comments</u>. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444, or telephone (513) 296-5377.

6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-M-38510 and MIL-STD-1331, and as follows:

GND	Ground zero voltage potential.
	Quiescent supply current.
$I_{\rm H}^{\rm cc}$	Input current low.
	Input current high.
T _C "	Case temperature.
T _A	Ambient temperature.
V.cc	Positive supply voltage.
C_{TN}	Input terminal-to-GND capacitance.
C _{PD}	Power dissipation capacitance.
V _{IC+}	Positive input clamp voltage.
V _{1C}	Negative input clamp voltage.
	Trigger duration (width).
07V	Latch-up over-voltage.
0/I	Latch-up over-current.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER	SIZE		5962-92183
DAYTON, OHIO 45444		REVISION LEVEL	SHEET 21

DESC FORM 193A JUL 91

9004708 0005632 063 🔳

Military documentation format	Example PIN under new system	Manufacturing source listing	Document listing
New MIL-M-38510 Military Detail Specifications (in the SMD format)	5962-XXXXXZZ(B or S)YY	QPL-38510 (Part 1 or 2)	MIL-BUL-103
New MIL-H-38534 Standardized Military Drawings	5962-XXXXXZZ(H or K)YY	QML-38534	MIL-BUL-103
New MIL-I-38535 Standardized Military Drawings	5962-XXXXXZZ(Q or V)YY	QML-38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standardized Military Drawings	5962-XXXXXZZ(M)YY	MIL-BUL-103	MIL-BUL-103

6.7 Sources of supply.

6.7.1 <u>Sources of supply for device classes B and S</u>. Sources of supply for device classes B and S are listed in QPL-38510.

6.7.2 <u>Sources of supply for device classes Q and V</u>. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.

6.7.3 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.

STANDARDIZED MILITARY DRAWING DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444	SIZE A		5962-92183
		REVISION LEVEL	SHEET 22

DESC FORM 193A JUL 91

9004708 0005633 TTT 📟